## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ocket Number (Optional) PKHF-04053US Applicantes Noboru ICHIN PER REC' PCT/PTO 07 FEB 2006

Concurrently Herewith Not Yet Assigned U.S. PATENT DOCUMENTS EVAMINED SUBCLASS FILING DATE NAME CLASS DOCUMENT NUMBER DATE INITIAL IF APPROPRIATE U.S. PATENT APPLICATION PUBLICATIONS EXAMINE FILING DATE NAME CLASS SUBCLASS REF DOCUMENT NUMBER DATE INITIAL IF APPROPRIATE FOREIGN PATENT DOCUMENTS SUBCLASS Translation REF DOCUMENT NUMBER DATE COUNTRY CLASS YES NO 2003-46128 02/14/2003 JAPAN ABS ABS 2000-349336 12/15/2000 JAPAN OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Yang, Ying-Ge, "Preparation and Structural Properties for GaN Films Grown on Si (1 1 1) by Annealing", Applied Surface Science, Vol. 193, 2002, pages 254 -260 DATE CONSIDERED EXAMINER 08/01/2008

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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